

Product Change Notification / SYST-23YLWV584

Date:

24-Aug-2023

Product Category:

Power Discrete Components

PCN Type:

Document Change

Notification Subject:

Data Sheet - MSC080SMA120B4 1200V 80 m Ω mSiC MOSFET TO-247-4

Affected CPNs:

SYST-23YLWV584_Affected_CPN_08242023.pdf SYST-23YLWV584_Affected_CPN_08242023.csv

Notification Text:

SYST-23YLWV584

Microchip has released a new Datasheet for the MSC080SMA120B4 1200V 80 m Ω mSiC MOSFET TO-247-4 of devices. If you are using one of these devices please read the document located at MSC080SMA120B4 1200V 80 m Ω mSiC MOSFET TO-247-4.

Notification Status: Final

Description of Change: • Updated typical value for zero gate voltage drain current in Table 1-3. • Updated typical values for diode forward voltage in Table 1-5. • Updated Figure 1-7 and Figure 1-13.

Impacts to Data Sheet: None

Reason for change: To improve Productivity. Change Implementation Status: Complete

Date Document Changes Effective: 24 Aug 2023

NOTE: Please be advised that this is a change to the document only the product has not been changed.

Markings to Distinguish Revised from Unrevised Devices: N/A

Attachments:

MSC080SMA120B4 1200V 80 mO mSiC MOSFET TO-247-4

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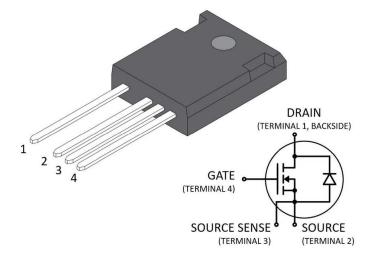
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MSC080SMA120B4



Product Overview

1200V, 80 m Ω typical at 20 V_{GS}, Silicon Carbide (SiC) N-Channel MOSFET, TO-247 4-lead with a source sense.



Features

- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, T_{l(max)} = 175 °C
- Fast and reliable body diode
- Superior avalanche ruggedness
- RoHS compliant

Benefits

- High efficiency to enable lighter and more compact system
- Simple to drive and easy to parallel
- · Improved thermal capabilities and lower switching losses
- Eliminates the need for external freewheeling diode
- Lower system cost of ownership

Applications

- Photovoltaic (PV) inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- Induction heating and welding
- Hybrid Electric Vehicle (HEV) powertrain and Electric Vehicle (EV) charger
- Power supply and distribution

1. Device Specifications

This section shows the specifications of this device.

1.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings of this device.

Symbol	Parameter	Ratings	Unit
V _{DSS}	Drain source voltage	1200	V
I _D	Continuous drain current at T _C = 25 °C	40	А
	Continuous drain current at T_C = 100 °C	28	
I _{DM}	Pulsed drain current ¹	90	
V _{GS}	Gate-source voltage	23 to -10	V
	Transient gate-source voltage	25 to -12	
P _D	Total power dissipation at $T_C = 25 \text{ °C}$	231	W
	Linear derating factor	1.54	W/°C

Table 1-1. Absolute Maximum Ratings

Note:

1. Repetitive rating: pulse width and case temperature are limited by the maximum junction temperature.

The following table shows the thermal and mechanical characteristics of this device.

Table 1-2. Thermal and Mechanical Characteristics

Symbol	Characteristic/Test Conditions	Min.	Тур.	Max.	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance	—	0.50	0.65	°C/W
Tj	Operating junction temperature	-55	—	175	°C
T _{STG}	Storage temperature	-55	—	150	°C
TL	Lead temperature for 10 seconds	—	—	300	°C
_	Mounting torque, 6-32 or M3 screw	—	—	10	lbf.in
		—	—	1.1	N.m
Wt	Package weight	_	0.22	-	oz
		—	6.2	_	g

ESD practices should comply with JESD-625.

1.2 Electrical Performance

The following table lists the static characteristics of this device. $T_1 = 25$ °C unless otherwise specified.

Table 1-5						
Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V_{GS} = 0V, I _D = 100 µA	1200	—	—	V
R _{DS(on)}	Drain-source on resistance ¹	V _{GS} = 20V, I _D = 15A	—	80	100	mΩ
V _{GS(th)}	Gate-source threshold voltage	$V_{GS} = V_{DS}$, $I_D = 1 \text{ mA}$	1.9	3.0	4.5	V
I _{DSS}	Zero gate voltage drain current	V _{DS} = 1200V, V _{GS} = 0V	—	0.2	100	μΑ
		V_{DS} = 1200V, V_{GS} = 0V, T_{J} = 175 °C	—	2	—	
I _{GSS}	Gate-source leakage current	V _{GS} = 20V/-10V	_	_	±100	nA

Table 1-3. Static Characteristics



Note:

1. Pulse test: pulse width < 380 μ s, duty cycle < 2%.

The following table shows the dynamic characteristics of this device. T_J = 25 °C unless otherwise specified. The dynamic characteristics are characterized, not 100% tested, at the recommended operating V_{GS} = 20V/–5V.

	Table 1-4.	Dynamic	Characteristics
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Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance	$V_{GS} = 0V$	—	1100	—	рF
C _{rss}	Reverse transfer capacitance	V _{DD} = 1000V	—	6.2	—	
C _{oss}	Output capacitance	V _{AC} = 25 mV f = 200 kHz	—	91	—	
Qg	Total gate charge	$V_{GS} = -5V/20V$	—	64	—	nC
Q _{gs}	Gate-source charge	V _{DD} = 800V	—	12	—	
Q _{gd}	Gate-drain charge	I _D = 15A	—	19	—	
t _{d(on)}	Turn-on delay time	V _{DD} = 850V	—	13	—	ns
t _r	Voltage rise time	$V_{GS} = -5V/20V$	—	11	—	
t _{d(off)}	Turn-off delay time	I _D = 20A	—	22	—	
t _f	Voltage fall time	$R_{g(ext)} = 8\Omega$	—	12	—	
E _{on}	Turn-on switching energy	Freewheeling diode = MSC080SMA120B4 ($V_{GS} = -5V$); reference Figure 1-17	_	469	—	μJ
E _{off}	Turn-off switching energy	$(V_{0}) = -5V$, reference right $-1V$	—	47	—	
ESR	Gate equivalent series resistance	f = 1 MHz, 25 mV, drain short	—	1.9	—	Ω
SWCT	Short circuit withstand time	V _{DS} = 960V, V _{GS} = 20V	—	3	—	μs
E _{AS}	Avalanche energy, single pulse	V _{DS} = 150V, I _D = 15A	—	100	_	mJ

The following table shows the body diode characteristics of this device. $T_J = 25$ °C unless otherwise specified.

Table 1-5. Body Diode Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V _{SD}	Diode forward voltage	I _{SD} = 15A, V _{GS} = 0V	—	3.7	—	V
		I _{SD} = 15A, V _{GS} = -5V	—	3.9	—	
t _{rr}	Reverse recovery time	I_{SD} = 20A, V_{DD} = 850V, V_{GS} = -5V,	_	12	—	ns
Q _{rr}	Reverse recovery charge	dl/dt = –1000 A/ μ s, Drive Rg = 8 Ω	_	416	—	nC
I _{RRM}	Reverse recovery current		_	59	_	А



1.3 Typical Performance Curves

Data for performance curves are characterized, not 100% tested.

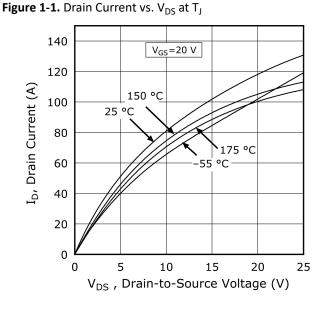
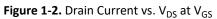


Figure 1-3. Drain Current vs. V_{DS} at V_{GS}



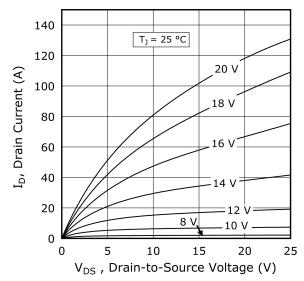
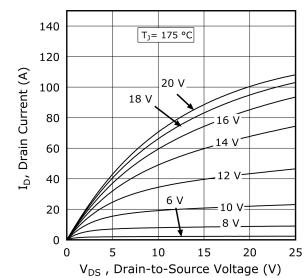
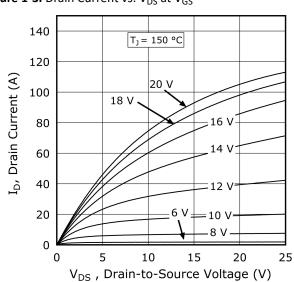


Figure 1-4. Drain Current vs. V_{DS} at V_{GS}





Міскоснір

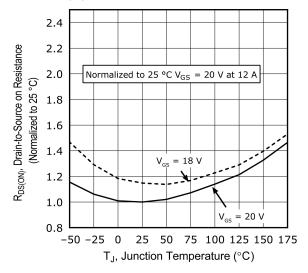


Figure 1-5. R_{DS(on)} vs. Junction Temperature

Figure 1-7. Capacitance vs. Drain-to-Source Voltage

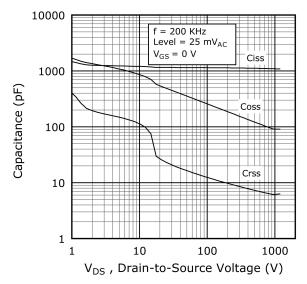


Figure 1-6. Gate Charge Characteristics

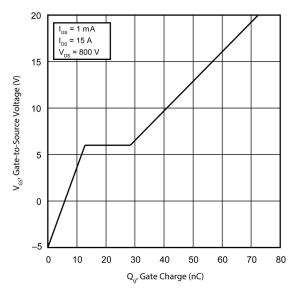
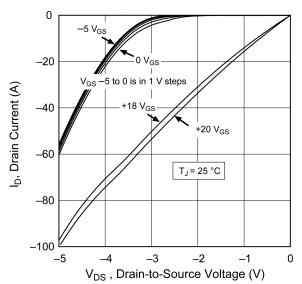


Figure 1-8. I_D vs. $V_{DS}\,3^{rd}$ Quadrant Conduction





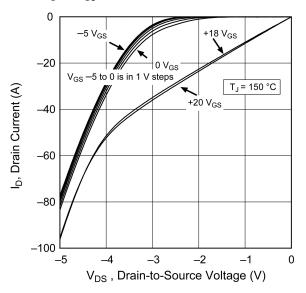


Figure 1-9. I_D vs. V_{DS} 3rd Quadrant Conduction

Figure 1-11. Switching Energy Eoff vs. V_{DS} & I_D

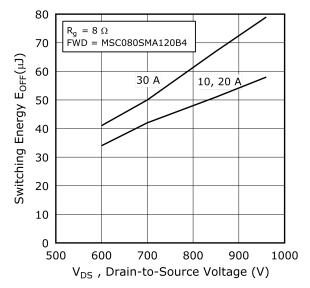


Figure 1-10. Switching Energy $E_{on}\,vs.\,V_{DS}\,\&\,I_{D}$

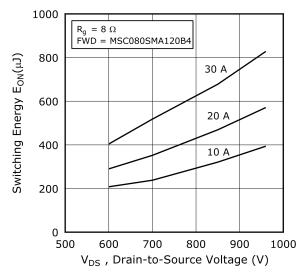
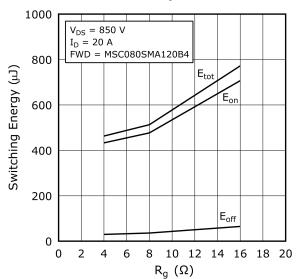


Figure 1-12. Switching Energy vs. R_g





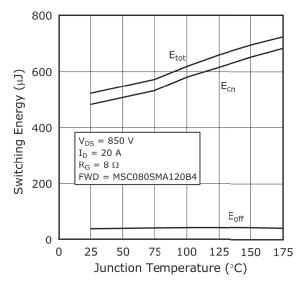
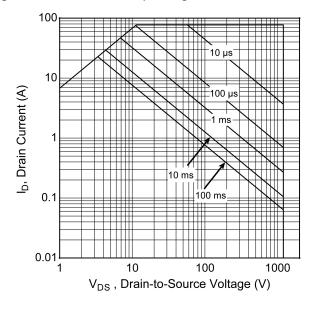
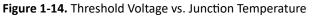
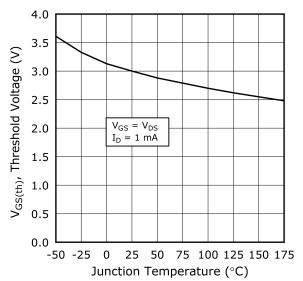


Figure 1-13. Switching Energy vs. Junction Temperature

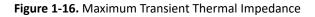
Figure 1-15. Forward Safe Operating Area

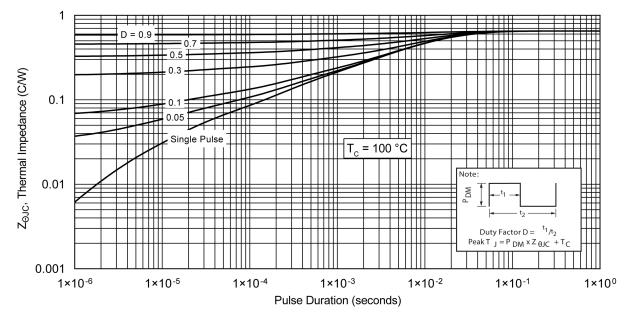






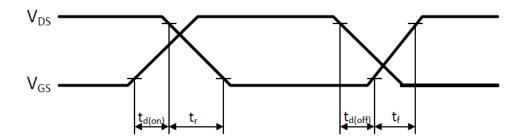






The following figure shows the switching waveform diagram of this device.

Figure 1-17. Switching Waveform





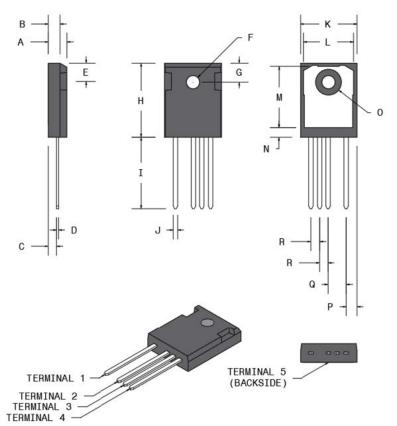
2. Package Specification

This section shows the package specification of this device.

2.1 Package Outline Drawing

The following figure illustrates the TO-247-4L package outline of this device.

Figure 2-1. Package Outline Drawing



The following table shows the TO-247-4L dimensions and must be used in conjunction with the package outline drawing.

Table 2-1. TO-247-4L Dimensions				
Symbol	Min. (mm)	Max. (mm)	Min. (in.)	Max. (in.)
A	4.90	5.17	0.193	0.204
В	1.85	2.11	0.073	0.083
С	2.25	2.51	0.089	0.099
D	0.55	0.68	0.022	0.027
Е	5.49	5.74	0.216	0.226
F	3.56	3.66	0.140	0.144
G	6.15 BSC		0.242 BSC	
Н	20.83	21.08	0.820	0.830
I	19.81	20.32	0.780	0.800
J	1.07	1.33	0.042	0.052
К	15.77	16.03	0.621	0.631



continue	d				
Symbol	Min. (mm)	Max. (mm)	Min. (in.)	Max. (in.)	
L	13.89	14.15	0.547	0.557	
Μ	16.25	16.85	0.640	0.663	
Ν	2.00	2.75	0.079	0.108	
0	7.10	7.50	0.280	0.295	
Ρ	2.87 BSC		0.113 BSC		
Q	5.08 BSC		0.200 BSC		
R	2.54 BSC		0.100 BSC		
Terminal 1	Drain				
Terminal 2	Source				
Terminal 3	Source sense				
Terminal 4	Gate				
Terminal 5	Drain				



3. Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

Table 3-1. Revision History

Revision	Date	Description
С	08/2023	The following changes are made in this revision of the document:
		• Updated typical value for zero gate voltage drain current in Table 1-3.
		• Updated typical values for diode forward voltage in Table 1-5.
		• Updated Figure 1-7 and Figure 1-13.
В	12/2022	 Updated values in Table 1-4. Updated values in Table 1-3. Updated Figure 1-14.
A	08/2022	Document migrated from Microsemi template to Microchip template; Assigned Microchip literature number DS-00004673A, which replaces the previous Microsemi literature number 050-7755.
Initial release (Microsemi Revision A)	09/2019	Document created.



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